

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	187811	(hole or via or gap or cut) near4 (electrode or pad)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 14:35
2	BRS	L2	482160	through-hole or (through adj hole)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 14:35
3	BRS	L3	18561	1 same 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 14:35
4	BRS	L4	485478	semiconductor adj device	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 14:35
5	BRS	L5	2820	3 and 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 14:36

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	23292	electroless adj plating	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 14:36
7	BRS	L7	215	5 and 6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 14:36
8	BRS	L8	125	7 and ((@ad<20010122) or (@rlad<20010122))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 14:37
9	IS&R	L10	525	(438/639).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 16:01
10	BRS	L13	182688 3	pad or electrode	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 16:12

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L14	32	9 and 13 and 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 16:25
12	BRS	L15	23	10 and 13 and 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 16:29
13	BRS	L16	31 °	11 and 13 and 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 16:32
14	BRS	L17	72 °	12 and 13 and 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 16:33
15	IS&R	L18	407	(438/640).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 17:16

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	IS&R	L19	710	(438/638).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 18:02
17	IS&R	L20	248	(438/667).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/20 18:31